

N-Channel Enhancement Mode MOSFET

TDM3442

DESCRIPTION

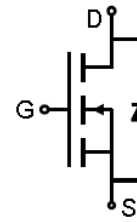
The TDM3442 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. This device is suitable for use as a load switch or in PWM applications.

GENERAL FEATURES

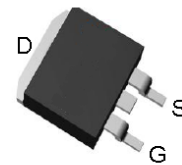
- $R_{DS(ON)} < 3.1m\Omega$ @ $V_{GS}=4.5V$
 $R_{DS(ON)} < 2.35m\Omega$ @ $V_{GS}=10V$
- High Power and current handling capability
- Lead free product is available
- Surface Mount Package

Application

- PWM applications
- Load switch
- Power management



Schematic diagram



Top View of TO-263-3

ABSOLUTE MAXIMUM RATINGS($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current @ Continuous (Note 1)	I_D ($T_C=25^\circ\text{C}$)	300	A
	I_D ($T_C=100^\circ\text{C}$)	220	A
Drain Current @ Current-Pulsed (Note 2)	I_{DM} ($T_C=25^\circ\text{C}$)	400	A
Drain Current @ Continuous (Note 1)	I_D ($T_A=25^\circ\text{C}$)	30	A
	I_D ($T_A=100^\circ\text{C}$)	25	A
Maximum Power Dissipation ($T_A=25^\circ\text{C}$)	P_D	2.5	W
Maximum Operating Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 To 150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	50	$^\circ\text{C}/\text{W}$
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ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

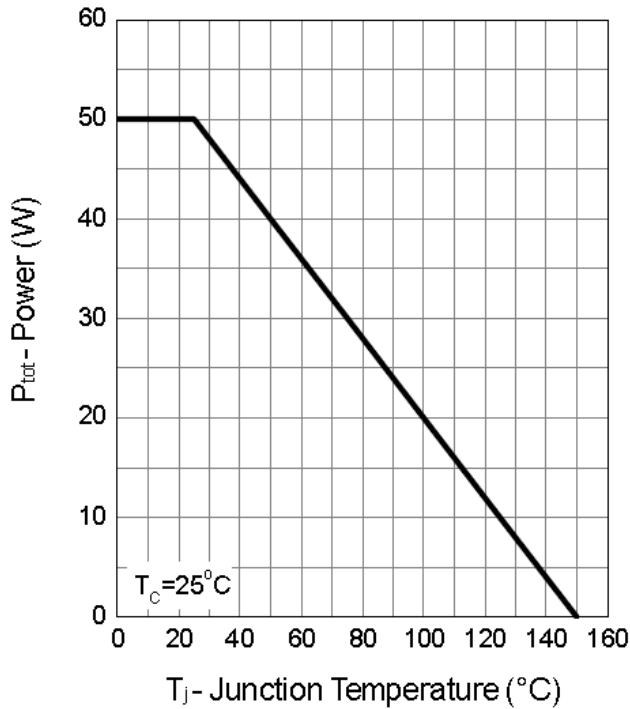
Parameter	Symbol	Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =24V,V _{GS} =0V			1	μ A
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V			± 100	nA
ON CHARACTERISTICS (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	1.35	1.7	2.4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =15A		2.9	3.1	mΩ
		V _{GS} =10V, I _D =20A		2.0	2.35	mΩ
DYNAMIC CHARACTERISTICS (Note4)						
Input Capacitance	C _{iss}	V _{DS} =15V,V _{GS} =0V, F=1.0MHz		2650		PF
Output Capacitance	C _{oss}			1790		PF
Reverse Transfer Capacitance	C _{rss}			120		PF
SWITCHING CHARACTERISTICS (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DS} =12V, R _L =2.1Ω, V _{GEN} =10V, R _G =2.9 Ω I _D =5.7A		14.3		nS
Turn-on Rise Time	t _r			26		nS
Turn-Off Delay Time	t _{d(off)}			24		nS
Turn-Off Fall Time	t _f			4.4		nS
Total Gate Charge	Q _g	V _{DS} =15V,I _D =20A,V _{GS} =4.5V		9.2		nC
Gate-Source Charge	Q _{gs}			6		nC
Gate-Drain Charge	Q _{gd}			2		nC
Body Diode Reverse Recovery Time	T _{rr}	I _F =20A, dI/dt=100A/μs		21		nS
Body Diode Reverse Recovery Charge	Q _{rr}			6.3		nC
DRAIN-SOURCE DIODE CHARACTERISTICS						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =20A		0.81	1.1	V

NOTES:

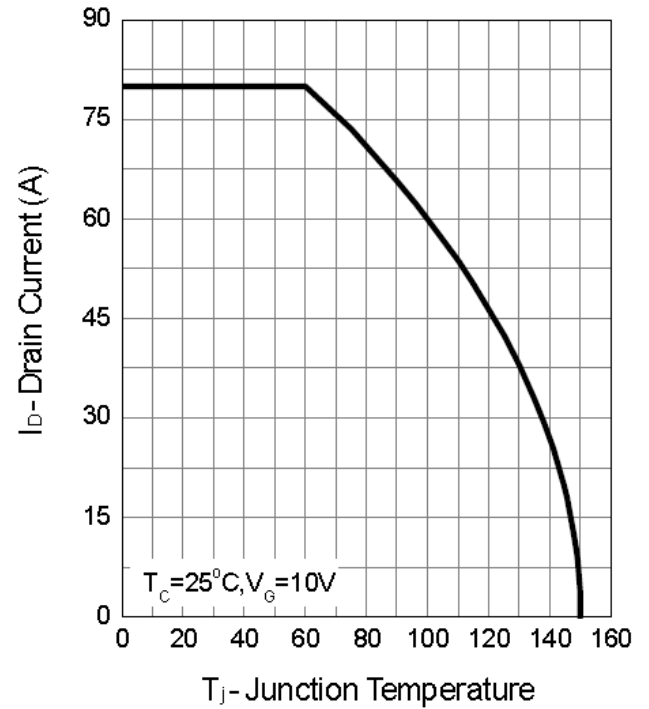
1. continue current is limited by bonding wire.
2. Pulse width limited by max. junction temperature.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production testing

Typical Operating Characteristics

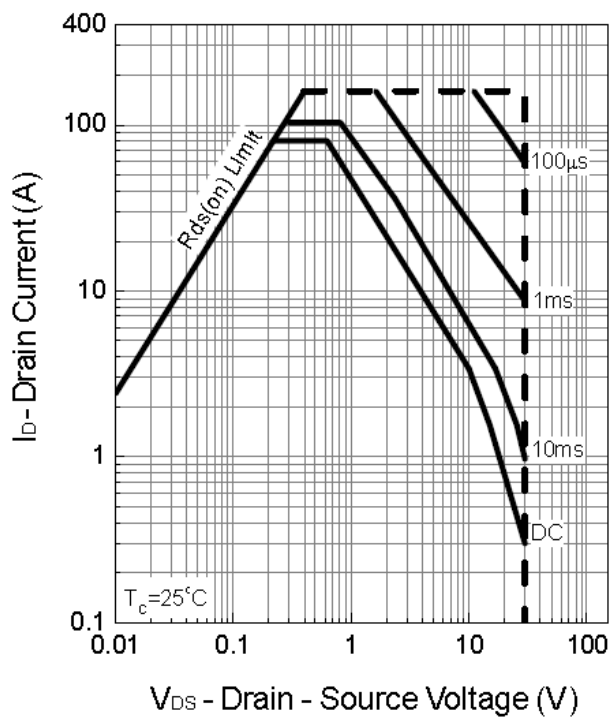
Power Dissipation



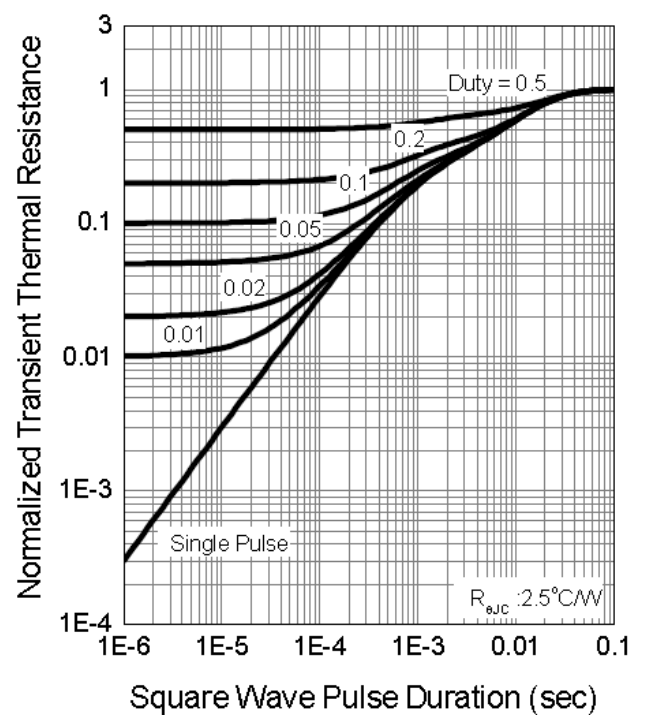
Drain Current



Safe Operation Area

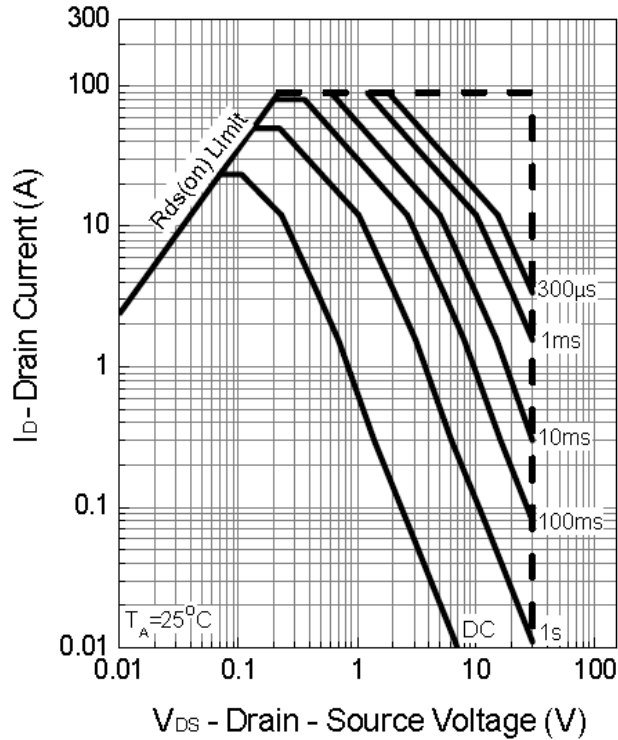


Thermal Transient Impedance

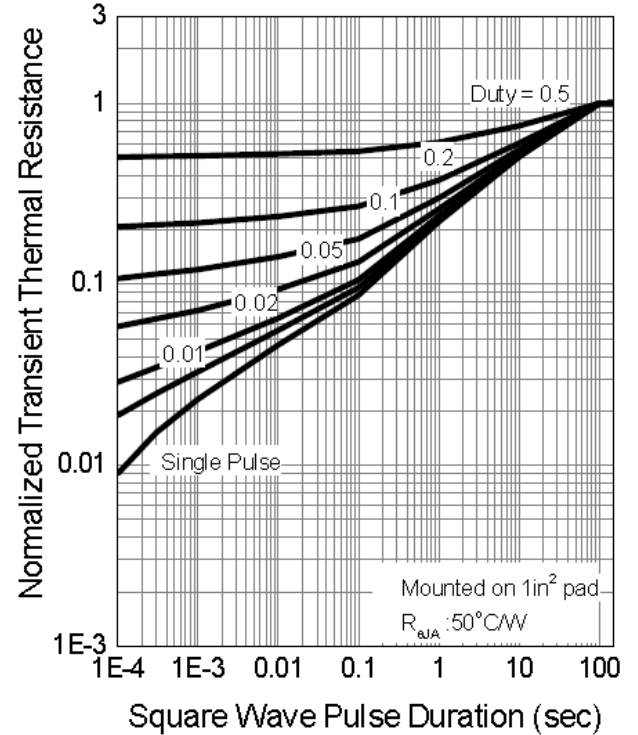


Typical Operating Characteristics(Cont.)

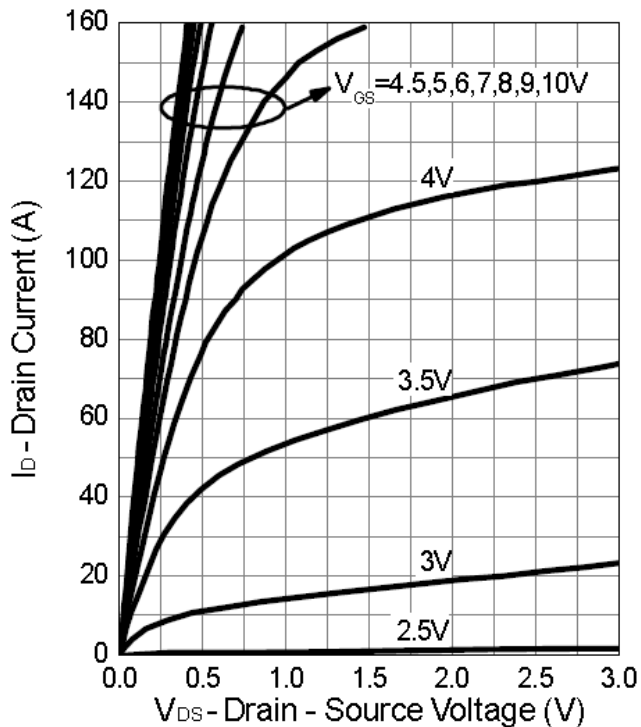
Safe Operation Area



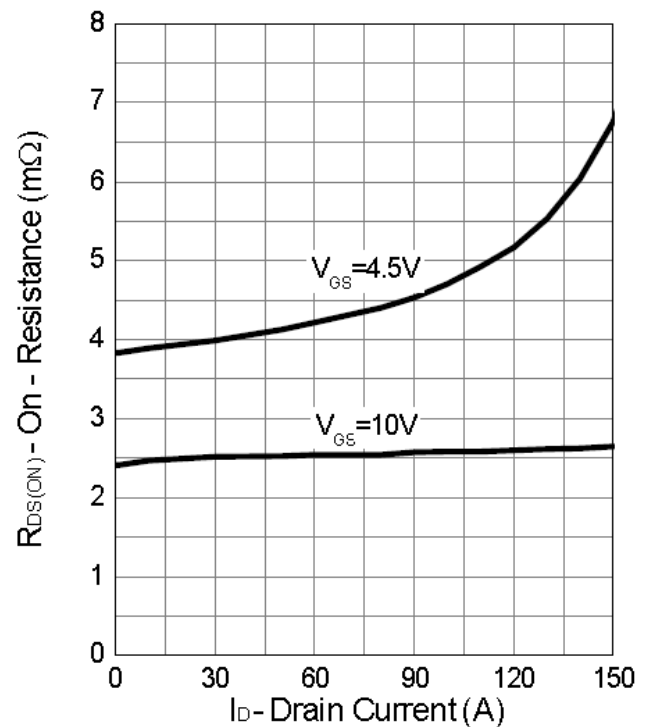
Thermal Transient Impedance



Output Characteristics

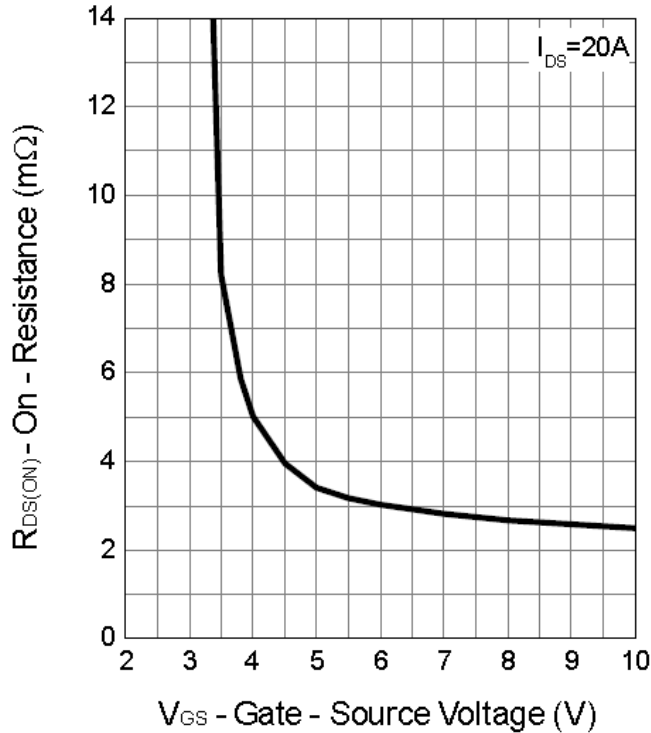


Drain-Source On Resistance

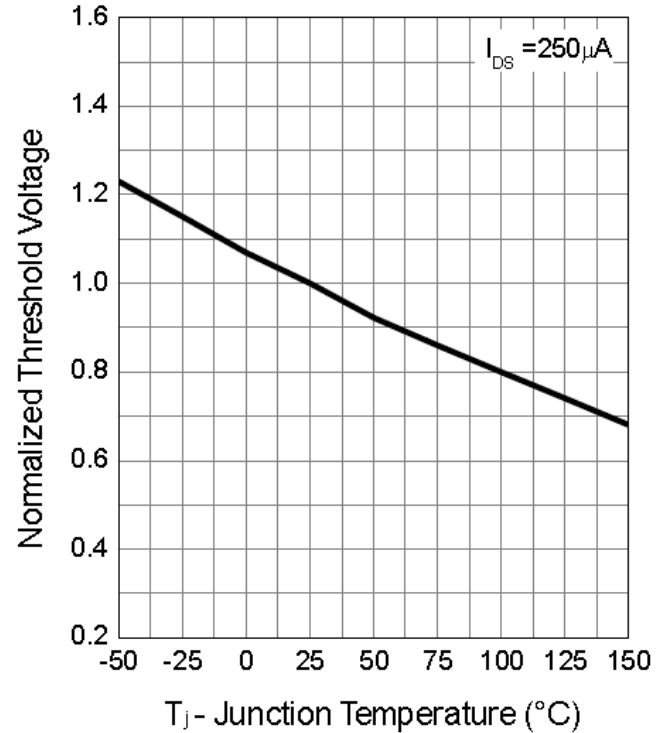


Typical Operating Characteristics (Cont.)

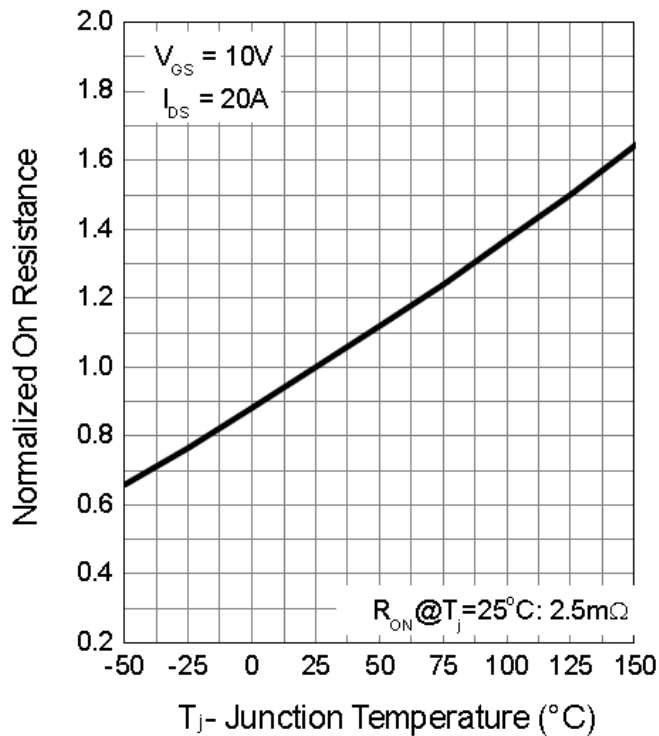
Gate-Source On Resistance



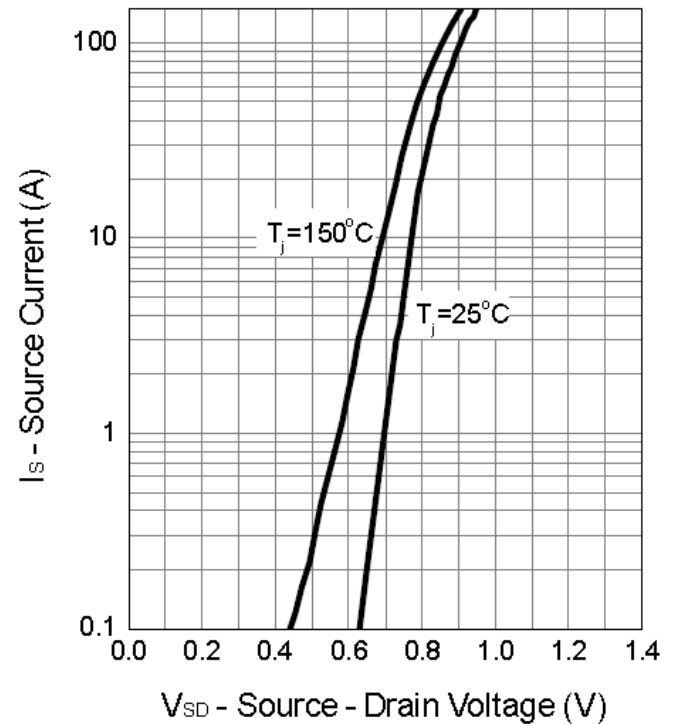
Gate Threshold Voltage



Drain-Source On Resistance

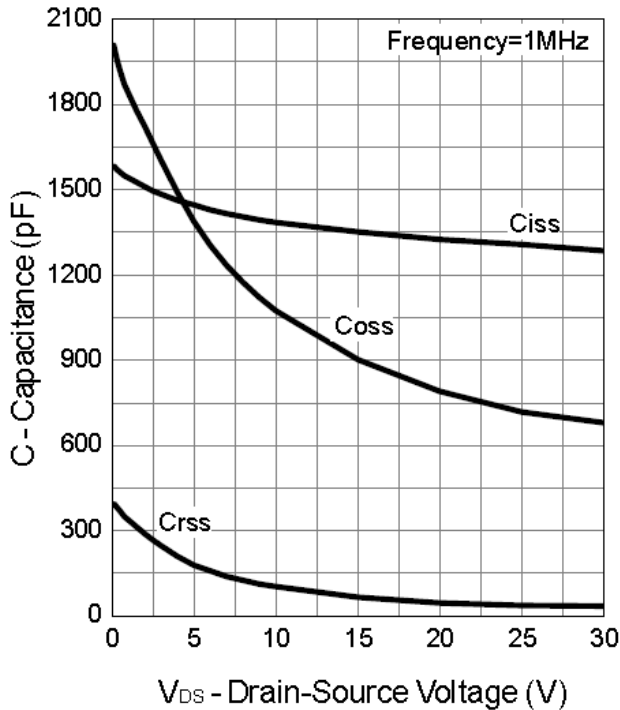


Source-Drain Diode Forward

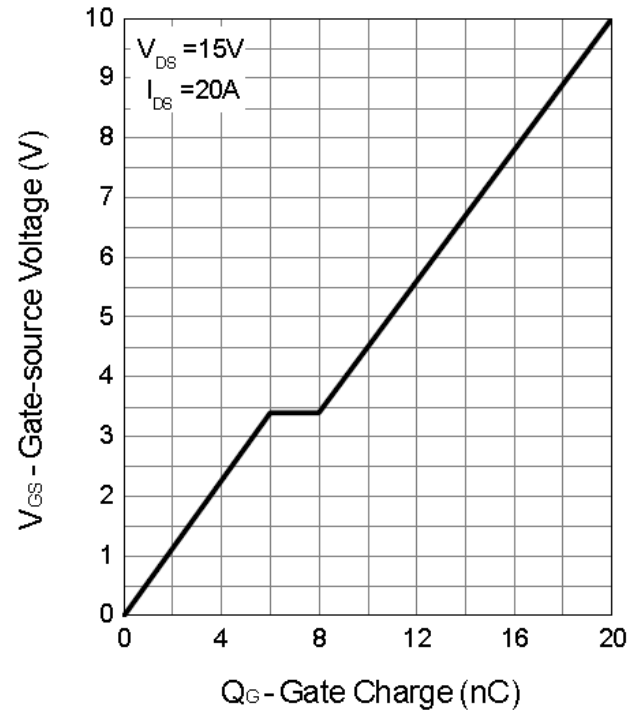


Typical Operating Characteristics (Cont.)

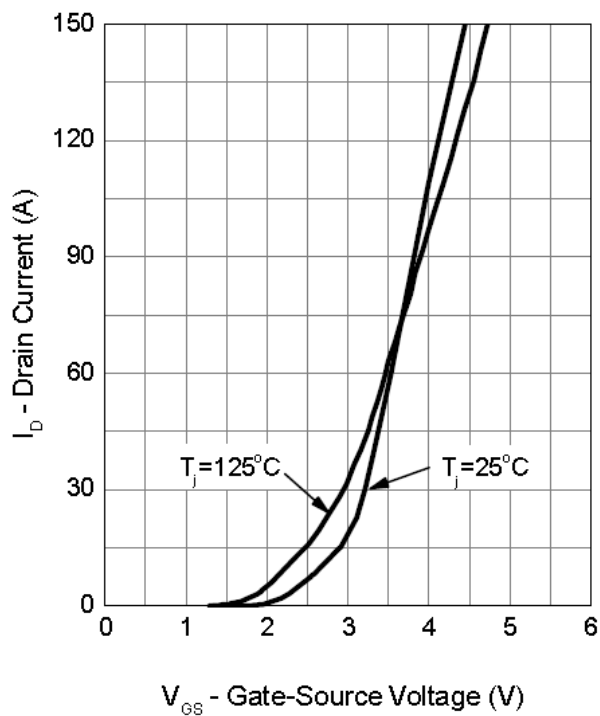
Capacitance



Gate Charge



Transfer Characteristics

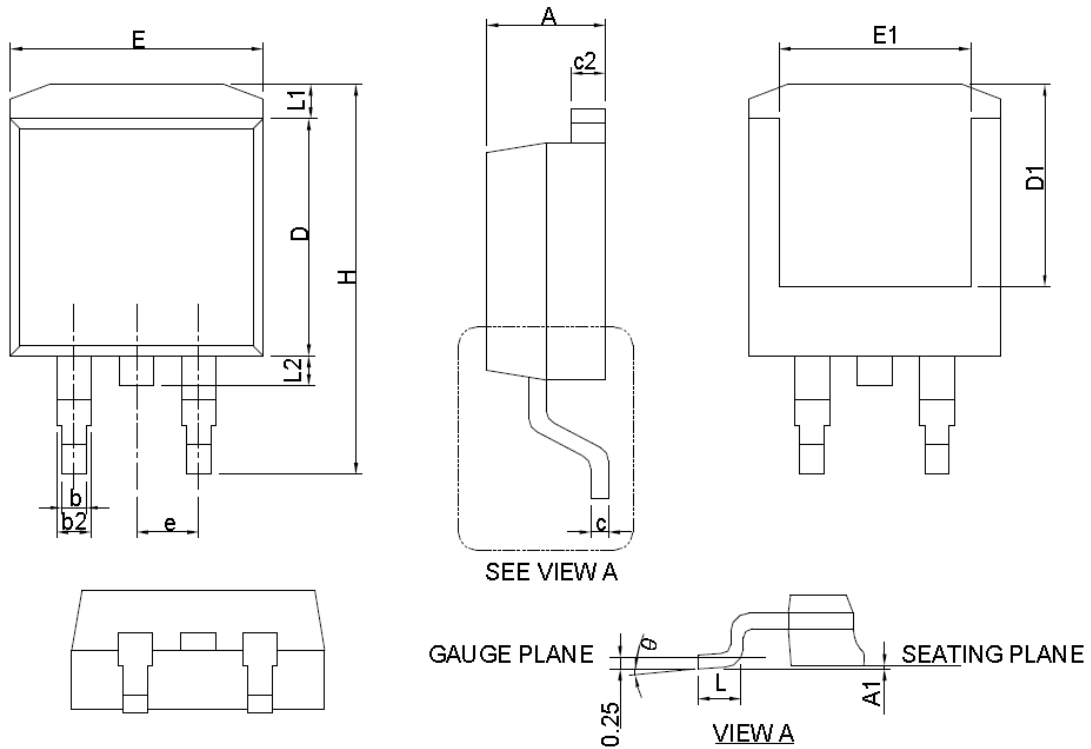


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Package Information

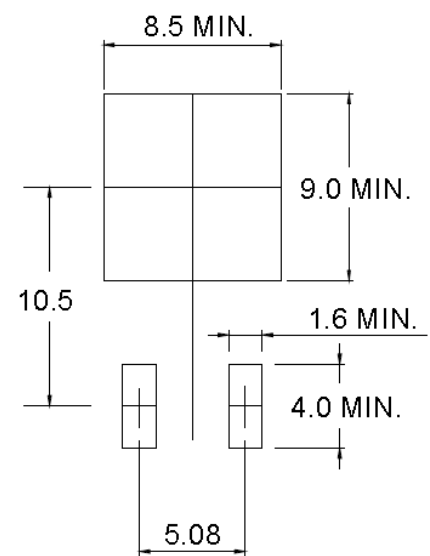
TO263-3 Package



SYMBOL	TO-263-3			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	0.00	0.25	0.000	0.010
b	0.51	0.99	0.020	0.039
b2	1.14	1.78	0.045	0.070
c	0.38	0.74	0.015	0.029
c2	1.14	1.65	0.045	0.065
D	8.38	9.65	0.330	0.380
D1	6.00	9.00	0.236	0.354
E	9.65	11.43	0.380	0.450
E1	6.22	9.00	0.245	0.354
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.68	-	0.066
L2	-	1.78	-	0.070
θ	0°	8°	0°	8°

Note : Follow JEDEC TO-263 AB.

RECOMMENDED LAND PATTERN



UNIT: mm

Design Notes